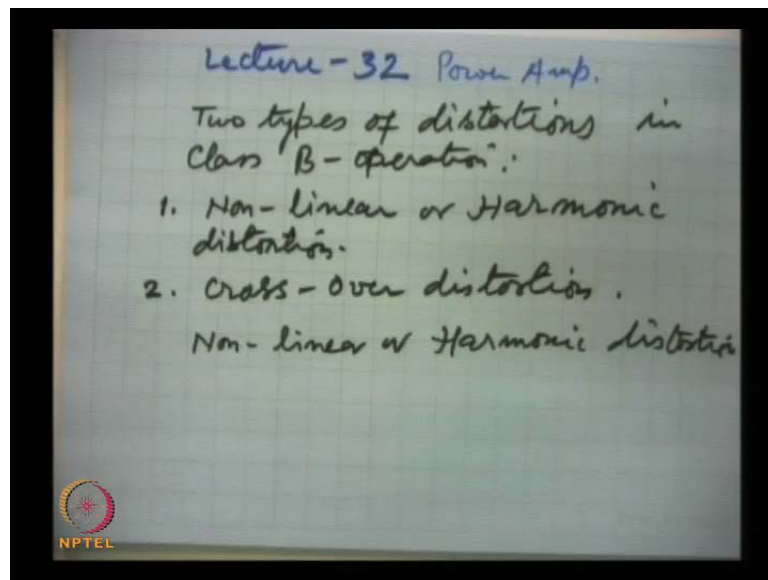


Electronics
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Module No. #06
Power Amplifiers
Lecture No. #03
Power Amplifiers (Contd.)

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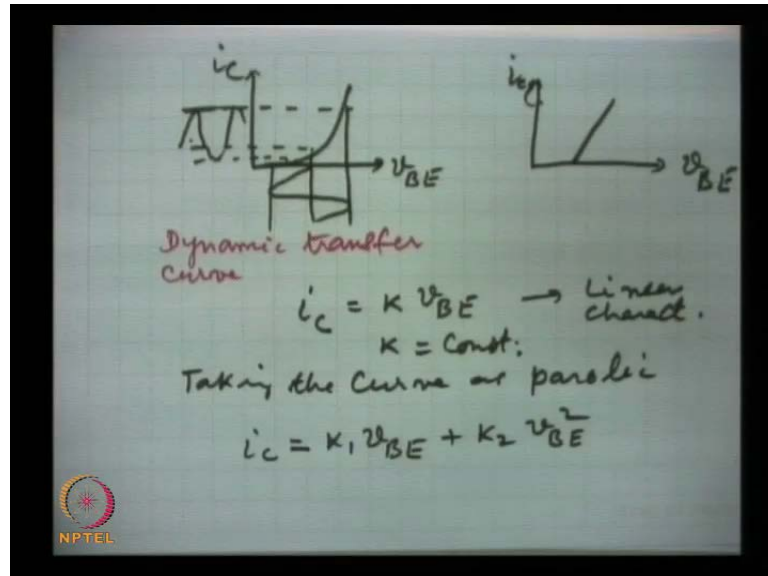


We were talking about the distortions in the output signal in the class B operation, and we said that there are two types of distortions. One is two types of distortions in class B operation: one was the non-linear, which is also called harmonic - harmonic distortion, and the other one is cross over distortion. Distortion implies these two kinds; for example, in the first one the signal frequency as well as its harmonics that is if ω is the angular frequency of the input signal, then at the output other than ω frequencies like 2ω , 3ω , 4ω the harmonics will also be present, they are distorted, and they are distortions.

And many applications will not except this distortion, the other one is cross over distortion. Now, we not only talk about these two distortions in details, but also the

remedies; that means class B operation finally we will see is free from both these kinds of a distortions. So, first we study the non-linear or harmonic distortion, we know that the current and voltage swings involved with the power amplifiers are large.

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Now, let us look at the trans conductance curve, dynamic trans conductance curve this is the output current and this is the voltage the input voltage now see here then the whole region of this characteristics will be involved when the output current swing for example has to be high, so let us look here; see the different regions of the input voltage they will give rise to different asymmetric output currents, and this is the net distortion, this is the dynamic transfer curve, in transfer curve 1 property, 1 parameter of output port is involved and the other parameter is from the other port, here output current versus input voltage that is transfer curve and it is non-linear, and we are going to use the whole part of it and this is bound to give the distortion and as a result of this non-linearity other than the signal frequency the multiples the harmonics will also be present,

Now, we analyze it and we will see that the output finally in the push pull case then there is a symmetrical design then the output will be free from even harmonics like the biggest distortion will be from if ω is the input frequency then 2ω the second harmonic will be have an largest magnitude amplitude of distortion that will be absent not only that although even harmonics will be absent finally, and odd as the number the 3

omega 5 omega they will be there, but their contributions will be negligibly small, so we continue with the simple analysis of these this distortion caused by this non-linearity.

For linear curve for example like this, **this** is the linear curve here it is i_c and this is a v_{BE} we can represent the for this linear case i_c the collector current this is i_c this is equal to K which is a constant that means k is proportional to the voltage this is the linear case where k is constant **k constant** and this is for linear characteristics but our curve is like this and this we can approximate for the simple analysis we can take it parabolic across the operating point, So, taking the curve as parabolic we can write this i_c as $k_1 v_{BE}$ plus $k_2 v_{BE}^2$ this is the equation parabolic, equation of a parabola.

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Input Signal
 $v_{BE1} = v_m \cos \omega t$
 Then,
 $i_c = k_1 v_m \cos \omega t + k_2 v_m^2 \cos^2 \omega t$
 $\cos^2 \omega t = \frac{1}{2} + \frac{1}{2} \cos 2 \omega t$
 $i_{c1} = I_{C1} + \gamma_0 + \gamma_1 \cos \omega t + \gamma_2 \cos 2 \omega t$
 $v_{BE2} = v_m \cos (\omega t + \pi)$
 $i_{c2} = I_{C2} + \gamma_0 - \gamma_1 \cos \omega t + \gamma_2 \cos 2 \omega t$

Now, let the input signal we take as a sinusoidal and it has the form the input signal v_{BE} is v_m the maximum amplitude $\cos \omega t$ where ω is the angular frequency of the signal so this is the equation of the input sinusoidal signal, then if we put this in this equation then we get i_c is $k_1 v_m \cos \omega t$ plus $k_2 v_m^2 \cos^2 \omega t$, now this $\cos^2 \omega t$ term can be written in a different form using the trigonometric relation and that relation is $\cos^2 \omega t$ is equal to half plus half $\cos 2 \omega t$, so we can replace that and then i_c will be any dc component present that is taken care by this term, plus these constants γ_0 plus $\gamma_1 \cos \omega t$ plus $\gamma_2 \cos 2 \omega t$ this is the expansion,

Now, for this in the push pull as we have talked that there are 2 transistors and the input signals are differing in phase by pi, the upper one responds the positive half of the input signal the lower half responds to the negative half, so writing the input for the second transistor as $v_m \cos \omega t + \pi$, since now we are using 2 transistors to this we can say 1 this is for upper transistor and for lower one we are writing, so we will get another equation i_{c2} in the similar way a simple equation and this i_{c1} for the upper half is i_{c2} , $\gamma_0 \cos \omega t + \gamma_2 \cos 2\omega t$, and if the final because both these currents are flowing through the common load.

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net current in the common load
 $i \propto (i_{c1} - i_{c2}) = X(i_{c1} - i_{c2})$
 $i' = 2 \times (\gamma_1 \cos \omega t)$
 $i = 2 \times (\gamma_1 \cos \omega t + \frac{\gamma_3}{3} \cos 3\omega t)$
 In symmetric design of push pull amplifier.
 $I_{c1} = I_{c2}$ (Trans)

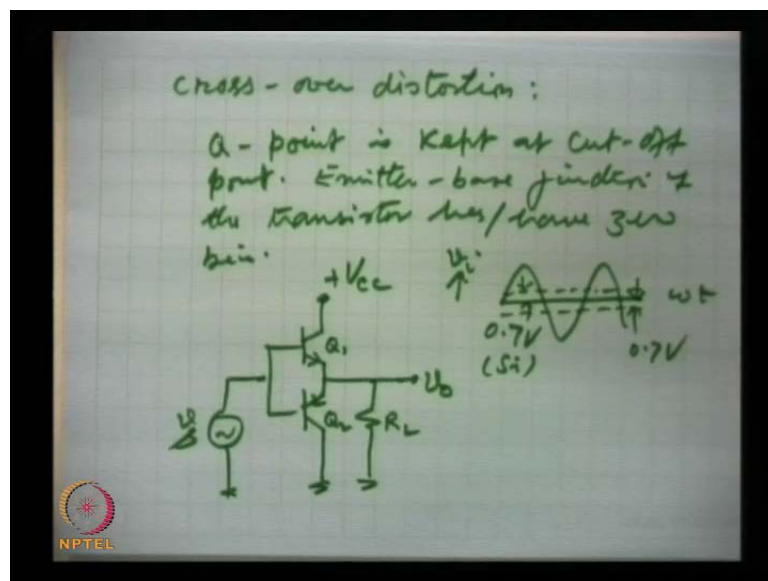
Then net current in the common load will be net current in the common load of the amplifier will be proportional to the difference i will be proportional to the difference of these 2 currents, and therefore we can write i will be equal to some constant X this is equal to X , $i_{c1} - i_{c2}$ so that will be $\gamma_1 \cos \omega t$, so we are seeing that second harmonic is completely absent and only pure signal frequency is there all harmonics are absent, but if we take a general case we took approximately parabolic shape of the v of the trans conductance curve, but in general case when Taylor series is used then actually this i we will find $2X$ into $\gamma_1 \cos \omega t + \gamma_3 \cos 3\omega t$ and so on,

In fact all the odd modes are present, but as I said as the order of the harmonic increases the amplitude falls, So, the contribution of γ_3 will be there but it is very small and

gamma5 will the cos that 5omega term that will be still a smaller, so this way and here we see the which take consideration of the dc currents, for the symmetric case have cancelled in this expression we have cancelled these capital c1, c2 the dc current, and this expression which has been written this is for the symmetric design which is always carried out for push pull amplifier, So, in symmetric design **in symmetric design** of push pull amplifiers in the above analysis we have taken ic1 equal to ic2 which is true for symmetric design so this is what we conclude from here.

The simple analysis shows that harmonic distortions are there but the biggest contribution in the distortion will come from the second harmonic which is absent in this because of the design of the push pull amplifier and in fact all the even harmonic are absent only odd harmonics are there but their amplitudes are negligibly a small then the cross over distortion.

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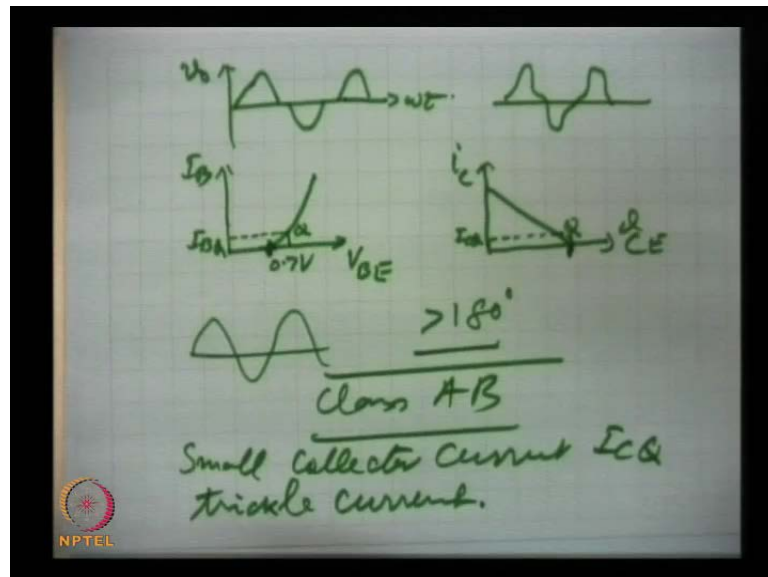


The next 1 is a cross over distortion, in class B operation the cut off condition is achieved by keeping the Q point at the cut off, Q point operating point is kept at cut off point, let us and at this point the emitter base junction **emitter base junction** of the transistor has or both have 0 bias, look at this design and then we will be able to explain that these are the 2 transistors Q1 and Q2, Q1 is n p n type and the other 1 is a p n p and both are biased by a single source V CC, and output is taken at the common load RL, if the input signal is like this; this is the input signal where this is voltage vi and this is

omega t or time, now in strictly speaking in the B operation the emitter base junction is at 0 potential, so and we remember that if the devices are of silicon then this transistor will not come to conduction state unless the emitter base junction is forward biased by 0.7 volts that is required.

In this case that means when the signal goes from 0 then first 0.7 milli volts will be used to forward biased only after 0.7 volts the conduction will start, similarly in the lower case up to 0.7 this transistor Q2 will not conduct, any nut shell here when this voltage is of 0.7 volts for a silicon device this transistor will not conduct for this part, similarly in the lower 1 this part of 0.7 it will not conduct, the 2 transistors will not conduct this 0.7 and this will amount 2 distortion in this fashion.

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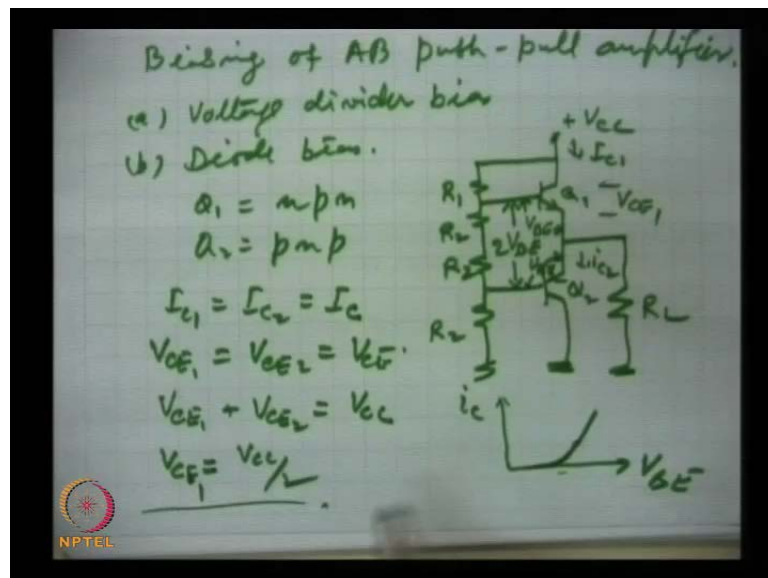


Output will be in little excruciating format it will be like this is V_{out} and this is ωt , but in practice also the outputs are like this, they are not the exact replica of the input signal, So, this distortion is known as cross over distortion, and this can be taken care of how to take care of that our input output curve is like this, I_B , this is base current and this is V_{BE} and this is the input curve, the strict B operation will imply to take the operating point here, instead of here we take a little we shift our operating point from here to here so this becomes the operating point, and this becomes the base current at the operating point,

Correspondingly this is the load line and the this is i_c and this is v_{CE} , at for class B operation the operating point at exactly cut off, but now we have moved so that the quotient current is not 0, here when this is done this is the Q has been shifted to this, this will take care of that 0.7 bias if that means this voltage this is 0.7 volts after we choose the operating point here, then these transistors are ready to conduct right from the beginning because 0.7 volt is already have been provided, similarly here 0.7 has been provided, so the output will be the way we expect replica of the input it will be only much higher in power.

Now, in shifting this the conductance is now more than for 180 degrees conduction angle little more, and this operation is class AB, why we do class AB operation because we want to get rid of the distortion which is called cross over distortion how we can take corrective measures by shifting the operating point from $I_{CQ} 0$ to a little bit value which may be 5 percent of the maximum value or even less and this operation is called class AB operation, and this current is small a small collector current **collector current** I_{CQ} is known as trickle current, trickle current so this trickle current provides the forward bias required and both the transistors are in the exact conduction state.

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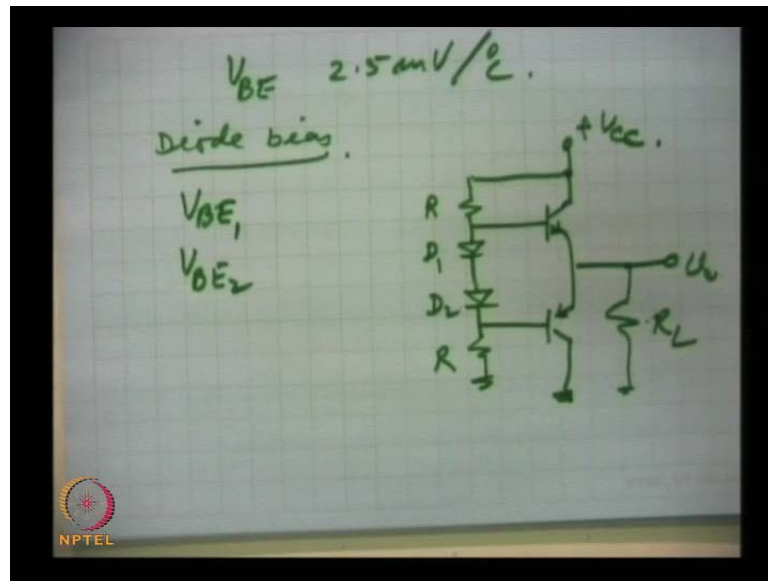
Now, briefly we take biasing of class AB push pull amplifiers biasing, there are 2 methods for biasing one is voltage divider, **voltage divider** bias and the other one is diode bias, now this is the complete design of class B push pull amplifier, Q_1 is this is voltage

divider bias and here this resistance R_1 , this is also R_1 , this is R_2 **this is R_2** , and this R_1 and R_2 they have been chosen such that the voltage developed across here is v_{BE} for this and v_{BE} for this transistor, that means $2V_{BE}$ so we have done voltage divider bias in the normally small signal amplifiers by very simple means we can calculate this resistance R_2 which is to be used, and Q_1 is of npn type and Q_2 is pnp type this is the push pull circuit which is very widely used,

And for the analysis purposes only half of the circuit can be taken because they are symmetric, so normally half is good enough to be taken into consideration, this voltage is V_{CE1} , similarly this voltage will be V_{CE2} this current is I_{c1} and here it will be I_{c2} and I_{c1} is equal to I_{c2} is equal to I_c , and V_{CE1} is equal to V_{CE2} which is equal to V_{CE} , and V_{CE1} plus V_{CE2} this is equal to V_{CC} , and hence V_{CE1} alone V_{CE1} this is V_{CC} half, if this is 10 volts 5 volts will be dropped here 5 volts will be dropped here that is the meaning this is showing, and so this is very simple design, and as I said we can take just upper half and we can calculate R_2 , same R_2 we have to use we have to take R_2 such that the voltage this voltage should be 0.7 volts, we can find out and this is the voltage divider bias.

There is a problem in the voltage divider bias if you look at the curve it is very sharp in the just one condition here, therefore a small changes in voltage V_{BE} , i_c trans conductance curve here the changes are very fast, and remember this thing and when we were talking of BJT

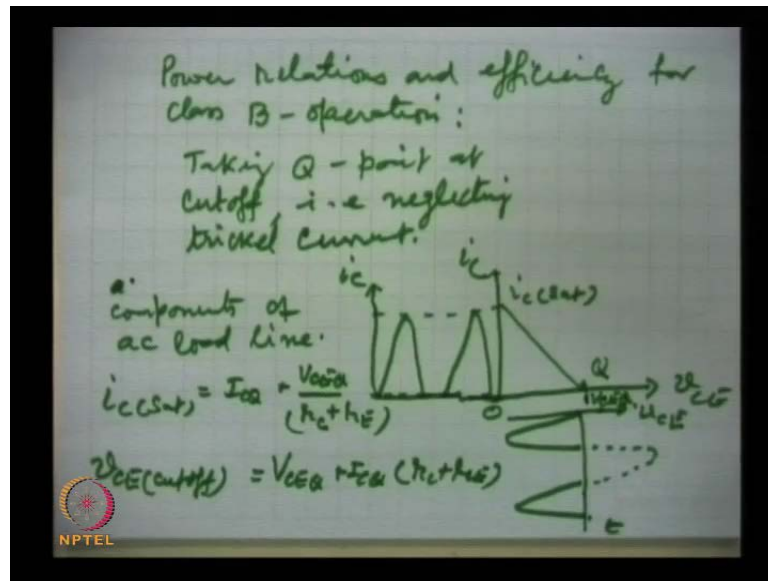
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We said that voltage V_{BE} is temperature dependent, with the it changes 2.5 milli volts per degree centigrade. So, this is for silicon transistor 700 milli volts, by if the temperature rises by 20 degrees then 50 milli volts change will be there, and 50 milli volts will amount to a large variation in this current here, therefore many times the resistance R_2 is replaced by the diode and then we call what is called diode bias. The characteristics of this diode are same as the characteristics of the emitter base junction of the 2 transistors, there is one thing that the pair of these 2 transistors along with these 2 diodes is available in the market for different power ranges for 5 watts, 10 watts, 50 watts.

The all the 4 pieces these 2 transistors complementary transistors 1 npn other pnp and these 2 diodes they are sold in a single pack and that makes life little easy, So, this is R, **this is R**, this is diode 1, this is diode 2, and this is the common route and we take the output here this is plus V_{CC} , this is the design of the diode bias, any changes of temperature will change V_{BE1} also V_{BE2} because the characteristics of these transistors are same as of these junction base emitter junctions are same as these diodes, So, same changes will occur in these diodes, they are and that will take corrective measures and the operating point will not shift because of this variation, temperature variation in particular, so this is about the diode bias.

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The next thing which we take are power relations and efficiency; **efficiency** for class B operation, this analysis is strictly for B operation that means we are neglecting the small effect of the trickle current which was required to eliminate cross over distortion, by neglecting by taking this trickle current is 0, we make the analysis much simple, and accuracy as I said few percent accuracy variations are always acceptable in electronics. So, not a big deal so taking the operating point taking Q point at cut off that is neglecting trickle current.

Then our this is the situation this is the ac load line and this is the operating point here this is i_c this is v_{CE} and this is t and this is v_{CE} and the corresponding currents this is i_c set this is ac load line and this is Q point this is 0 this is V_{CEQ} and the current will flow only for these half's, and it will be i_c like that, and we will take now that ac load line components you remember when we were talking about in the beginning of this module we spoke about the ac load line, the 2 equations which we got the ac components or the components of a c load line, we got two expressions i_c set was ICQ plus V_{CEQ} by effective collector and effective emitter resistance, and similarly we got v_{CE} at cut off equal to V_{CEQ} plus ICQ into r_C plus r_E , this 2 equations we got when we were talking about the ac load line, in this present case because the operating point we have taken at cut off and that is small trickle current we have neglected for the simplicity of the analysis, so ICQ we are taking as 0, So, if i_c is kept 0 here in these 2 equations

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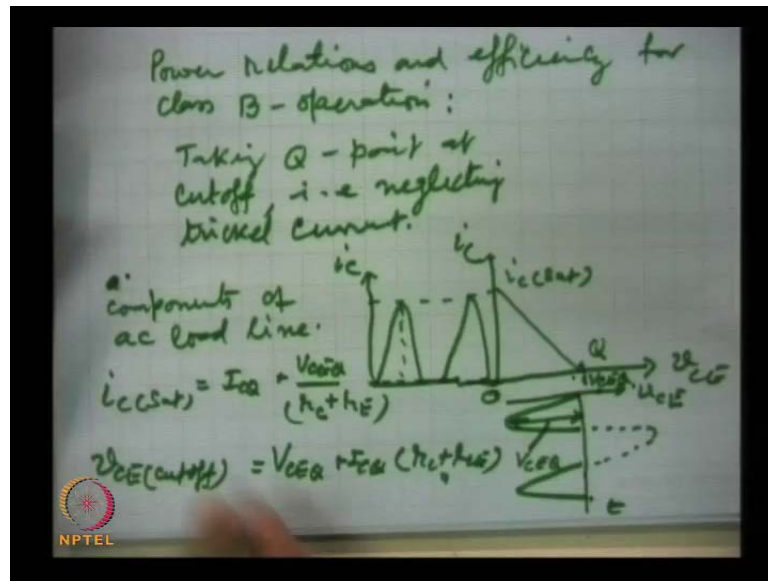
But $I_{CQ} = 0$ (B-operation)

$$i_{c(Sat)} = \frac{V_{CEQ}}{r_c + r_e}$$
$$V_{CE(cutoff)} = V_{CEQ}$$
$$V_{CEQ} = \frac{V_{CC}}{2} \quad (\text{when single dc source is used})$$
$$V_{CEQ} = V_{CC}$$

they are reduced to but I_{CQ} is 0 that is in B operation,

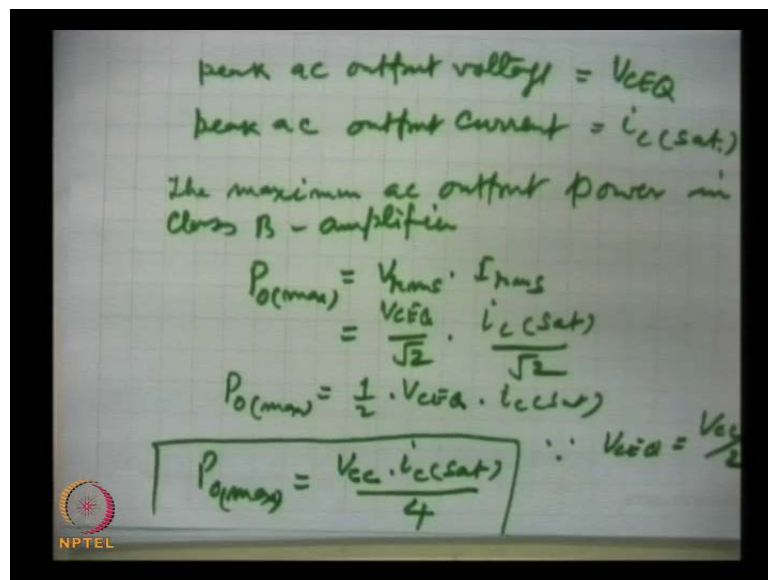
Therefore i_c set is equal to V_{CEQ} by r_c plus r_e , and similarly when we substitute I_{CQ} 0 in the voltage cut off at **cut off** equation we get it simply V_{CEQ} , So, this these 2 equations will help us in arriving at the maximum ac output power, further as earlier we have shown that V_{CEQ} is equal too, because the total voltage V_{CC} which we are applying here this is half appears here and **half appears here**, So, V_{CEQ} is equal to V_{CC} by 2 this is when we use single source voltage source, we can have a choice instead of biasing both transistors with a single source a positive voltage can be given at this collector in negative voltage we can give here, So, that this negative voltage will bias this collector in the reverse, and the upper one will be reverse bias by plus, so in that so this is single source when single dc source is used when 2 sources will be used then V_{CEQ} this is just for the sake of knowledge, we are using only one battery so for as this is true but other choices applicable that one voltage plus here, negative voltage here to reverse bias this collector in that case this V_{CEQ} will be equal to V_{CC} whatever we use so then we can write the expression the peak a c voltage.

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Let us this figure we should note this voltage here is V_{CEQ} so this voltage, this is V_{CEQ} , and this current is i_c set current because this point is 0 i_c current.

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So, the peak ac output voltage is V_{CEQ} , and peak a c output current this is i_c set saturation, then the maximum ac output power will be **the maximum ac output power** in class B amplifier this will be P_o max maximum is equal to V_{rms} into I_{rms} , and voltage rms this is the peak value and hence this is V_{CEQ} by root 2 this is i_c set **ic set** by root 2 so this is P_o maximum is equal to half V_{CEQ} into i_c set since V_{CEQ} is V_{CC} by 2 so P_o

max is equal to V_{CC} into i_c set by 4, this is an important relation and this will let us know the value of i_c saturation and what V_{CC} single dc source we are using to bias both the transistors, we know the magnitudes of these 2 parameters we can find out what will be the maximum output ac power available from the push pull amplifier.

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Efficiency:

$$\eta = \frac{P_o}{P_{dc}}$$

$$P_{dc} = V_{CEQ} \cdot I_{CQ}$$

$$I_{CQ} = \frac{1}{2\pi} \int_0^{\pi} i_c(\text{sat}) \sin \omega t \, d(\omega t)$$

$$I_{CQ} = \frac{i_c(\text{sat})}{\pi}$$

$$P_{dc} = V_{CEQ} \cdot I_{CQ} = \frac{V_{CEQ} \cdot i_c(\text{sat})}{\pi}$$

NPTEL

And then we can go for efficiency; and the efficiency this is convergence efficiency, that what fraction of the dc is available as ac, so convergence efficiency and this is we write as η and this is equal to P_o that ac output power by dc output power, and when it is to be expressed as a percent then we multiply this by hundred and this we have already find out the maximum output power, what will be the P_{dc} this is the maximum dc power which will be supplied to the circuit. The voltage is V_{CEQ} and this is I_{CQ} , now one thing is very important to remember that I_{CQ} is 0 because we have chosen the operating point at the cutoff point so in the absence of the signal the I_{CQ} is 0.

The transistors will come to the conduction state by the upper transistor will conduct because of the positive half, when positive half input signal is there then the transistor conducts, and when it conducts then we will have it draws dc power from the source, similarly; the lower transistor will be conducting for the negative half's of the input signal and then that transistor will consume the dc power and the current this i_c the current will flow, now so we can find out what is on an average what is the value of the collector current which is drawn from the battery, and this you might have done the

average over the period by using integration, so ICQ in half wave rectifiers this analysis has been done.

But, I just do it here; ICQ $\frac{1}{2\pi} \int_0^{2\pi} i_c \sin \omega t, d\omega t$, we have taken the signal as sinusoidal and the current which flows is this is the maximum current, and this is that sin part we solve it and we find that ICQ is $i_c \text{ set by } \frac{\pi}{2}$, therefore Pdc for 1 transistor is $V_{CEQ} \cdot ICQ$ which is $V_{CEQ} \cdot \frac{I_{c(sat)}}{2}$ now we substitute for ICQ so $i_c \text{ set by } \frac{\pi}{2}$, When similarly there will be a expression for the second transistor

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peak ac output voltage = V_{CEQ}
 peak ac output current = $i_{c(sat)}$
 The maximum ac output power in class B - amplifier

$$P_{0(max)} = V_{rms} \cdot I_{rms}$$

$$= \frac{V_{ceQ}}{\sqrt{2}} \cdot \frac{i_{c(sat)}}{\sqrt{2}}$$

$$P_{0(max)} = \frac{1}{4} \cdot V_{ceQ} \cdot i_{c(sat)}$$

$$\boxed{P_{0(max)} = \frac{V_{cc} \cdot i_{c(sat)}}{4}}$$

$$\therefore V_{ceQ} = \frac{V_{cc}}{2}$$

and therefore Pdc for transistors 1 and 2 that is for Q1 and Q2 both, Pdc this will be double of Pdc 1 which we have calculated, and this is $2V_{CEQ}$ into $i_c \text{ set by } \frac{\pi}{2}$, but $2V_{CEQ}$ is equal to V_{CC} , therefore Pdc is equal to $V_{CC} \cdot i_c \text{ set by } \frac{\pi}{2}$, this is the expression for the dc power which is taken from the dc power source, and we have already obtained the expression for the ac power which will be available at the load.

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$$\begin{aligned}\eta &= \frac{P_o}{P_{dc}} \times 100 \\ (\%) &= \frac{V_{cc} \cdot I_c(sat)}{4} \times \frac{\pi}{V_{cc} \cdot I_c(sat)} \times 100 \\ &= \frac{\pi}{4} \times 100 = \\ \eta &= \underline{78.5\%}\end{aligned}$$

NPTTEL

Therefore, the efficiency η in percent this will be P_o , P_{dc} into 100, and this is we substitute the values V_{CC} , I_c set by 4 into π by V_{CC} , I_c set into 100. So, they cancel and we are left with π by 4 into 100, and that comes out to be η comes out to be 78.5 percent, very high efficiency. So, this is of course, the theoretical highest possible efficiency 78.5 percent when the transistors are operating in class B as a class B amplifier. This efficiency for the class A power amplifier when the load was the (()) coupled it was 25 percent, here it is 78.5 percent which is quite high very high, and that is the reason one of the important reasons that class B push pull amplifiers are very widely used,

All the almost all public attires systems are class in fact A B operation because distortion has to be completely taken care of, So, A B operation and there the efficiency will slightly fall so the practical efficiency will be close to seventy or so, So, this is this, the last thing about class B operation;

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Power dissipation

$$P_D = \text{Power dissipation}$$
$$P_o = 5 P_D$$
$$\propto \frac{P_D}{5} = \frac{1}{5} P_o$$

V - FETS

We can say and that is about power dissipation that means how much power the transistors are suppose to dissipate the cost of the transistor will vary a transistor which can dissipate say 2 watts of power and 5 watts of power they will be quite different, 5 watts power dissipation transistor will be quite high in this case in class B operation, this power dissipation is very small the P D dissipation power dissipation, this is 1/5th of P_o, output power is 5 times of P D or P D is 1/5th of P_o. This is another point which goes in favor of class A class B push pull amplifiers, for if we want output power as say 50 watts or 100 watts, let us say P_o is 100 watts then we need transistors which can dissipate only 20 watts of power, So, this is a big game with game, with class B power amplifiers.

We have been discussing this these power amplifiers with BJT circuits, in fact MOSFETS can also be used instead of 2 transistors BJT we can use MOSFETS, and they are a special fat devices, fat transistors where there is a V groove in the device and these are called V type FETS V FETS, these can be used and the power amplifiers this class B amplifier can be constructed instead of by B J T we can use this.

Specially designed field effect transistors also, and another thing that we took a emitter follower circuit for the **for the** push pull amplifier, we can use the common emitter circuit also, and the design is quite simple, and in that case normally the transformer coupling will be used at the output, So, many times the push pull amplifier is constructed using 2 transistors in common emitter, and the output is coupled to the load through a

transformer coupling. So, this is all about class B operation, class B power amplifiers and the most popular one of this was push pull amplifiers.